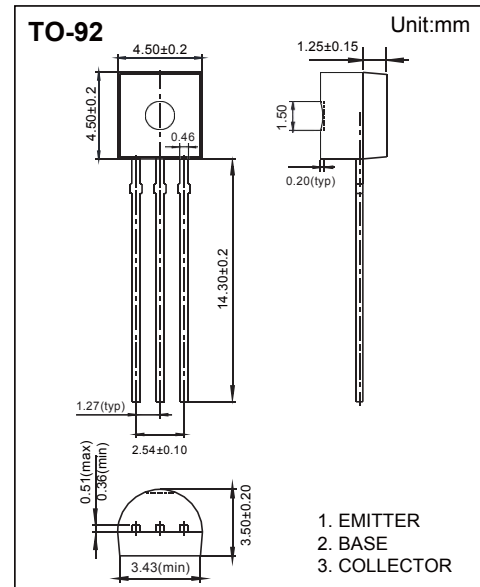


Transistor

NPN Transistors 2N2222

■ Features

- High current (max. 800 mA)
- Low voltage (max. 40 V)
- Complementary to 2N2907



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit	
Collector - Base Voltage	V _{CB0}	60	V	
Collector - Emitter Voltage	V _{CE0}	30		
Emitter - Base Voltage	V _{EB0}	5		
Collector Current - Continuous	I _C	0.8	A	
Peak Collector Current	I _{CM}	0.8		
Peak Base Current	I _{BM}	0.2		
Collector Power Dissipation	P _C	T _{amb} ≤ 25 °C	500	mW
		T _{case} ≤ 25 °C	1.2	W
Thermal Resistance From Junction to Ambient	R _{θJA}	350	°C/W	
Thermal Resistance From Junction to Case	R _{θJC}	146		
Junction Temperature	T _J	150	°C	
Storage Temperature	T _{stg}	-65 to 150		

Transistor

NPN Transistors

2N2222

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V _{CB0}	I _c = 100 μA, I _E =0	60			V
Collector- emitter breakdown voltage	V _{CE0}	I _c = 0.1 mA, I _B =0	30			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _c =0	5			
Collector cut-off current	I _{CB0}	V _{CB} = 50 V, I _E =0			10	nA
		V _{CB} = 50 V, I _E =0, T _{amb} =150 °C			10	μA
Emitter cut-off current	I _{EB0}	V _{EB} = 3V, I _c =0			10	nA
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =150 mA, I _B = 15mA			0.4	V
		I _c =500 mA, I _B = 50mA			1.6	
Base - emitter saturation voltage	V _{BE(sat)}	I _c =150 mA, I _B = 15mA			1.3	
		I _c =500 mA, I _B = 50mA			2.6	
DC current gain	h _{FE(1)}	V _{CE} = 10V, I _c = 0.1mA	35			
	h _{FE(2)}	V _{CE} = 10V, I _c = 1mA	50			
	h _{FE(3)}	V _{CE} = 10V, I _c = 10mA	75			
	h _{FE(4)}	V _{CE} = 1V, I _c = 150mA	50			
	h _{FE(5)}	V _{CE} = 10V, I _c = 150mA	100		300	
	h _{FE(6)}	V _{CE} = 10V, I _c = 500mA	35			
Turn-on time	t _{on}	I _{Con} = 150 mA; I _{Bon} = 15 mA; I _{Boff} = -15 mA			35	ns
Delay time	t _d				10	
Rise time	t _r				25	
Turn-off time	t _{off}				250	
Storage time	t _s				200	
Fall time	t _f				60	
Collector capacitance	C _{ob}	V _{CB} = 10V, I _E =I _e =0, f=1MHz			8	pF
Transition frequency	f _T	V _{CE} = 20V, I _c = 20mA, f=100MHz	250			MHz